# N-Channel 20-V (D-S) MOSFET

#### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
VDS (V)	$r_{DS(on)}(m\Omega)$	Id (A)		
20	9.5 @ V <sub>GS</sub> = 4.5V	16		
20	13 @ V <sub>GS</sub> = 2.5V	13		



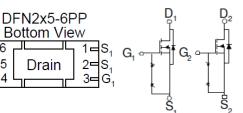
 $S_2 = 6$ 

 $S_{2} = 5$ 

-4

G\_2

Drain





FREE

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Limit	Units			
Drain-Source Voltage			20	V		
Gate-Source Voltage	V <sub>GS</sub>	±8	v			
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	l <sub>D</sub>	16	A		
	T <sub>A</sub> =70°C		11.3			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	50				
Continuous Source Current (Diode Conduction) <sup>a</sup>	۱ <sub>s</sub>	5.2	А			
Power Dissinction <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	3.5	w		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	U 'D	1.8	vv		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	36	°C/W		
	Steady State	ιν <sub>θ</sub> ja	76	C/VV		

Notes

- Surface Mounted on 1" x 1" FR4 Board. a.
- b. Pulse width limited by maximum junction temperature

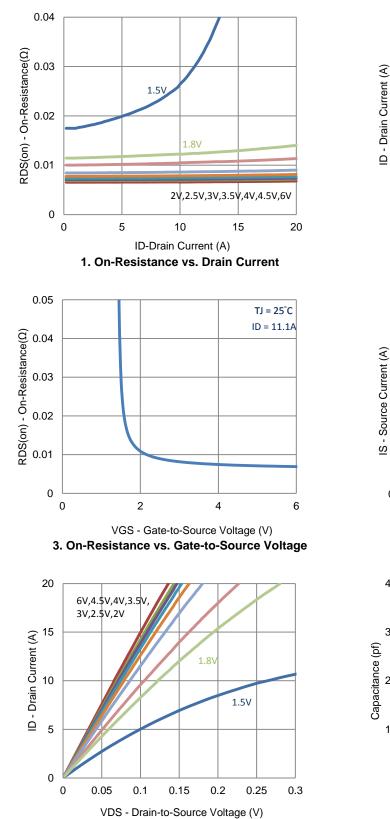
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	te-Source Threshold Voltage $V_{GS(th)}$ $V_{DS} = V_{GS}$ , $I_D = 250$ uA		0.4			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			±10	uA	
Zero Gate Voltage Drain Current		$V_{DS} = 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	uA	
	IDSS	$V_{DS} = 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	25			Α	
Drain Sauras On Desistance a	r	$V_{GS} = 4.5 \text{ V}, I_{D} = 11 \text{ A}$			9.5	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_{D} = 9 \text{ A}$			13	mt2	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 11 \text{ A}$		16		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 2.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.67		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Q <sub>g</sub>	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$		19			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10$ V, $V_{GS} = 4.3$ V, $I_{D} = 11$ A		3.4		nC	
Gate-Drain Charge	$Q_gd$			4.5			
Turn-On Delay Time	t <sub>d(on)</sub>			15			
Rise Time	t <sub>r</sub>	$V_{DS}$ = 10 V, $R_L$ = 1 $\Omega$ , $I_D$ = 11 A,		52		20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ = 4.5 V, $R_{GEN}$ = 6 $\Omega$		82		ns	
Fall Time	t <sub>f</sub>			35			
Input Capacitance	C <sub>iss</sub>			2109			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		204		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			201			

#### Notes

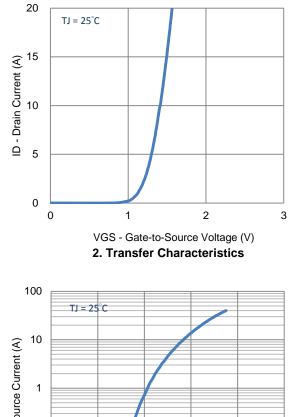
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

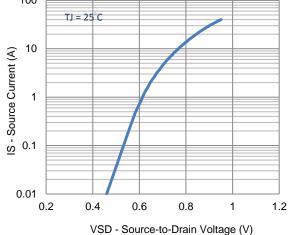
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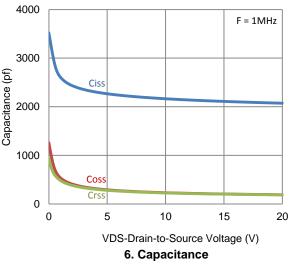
5. Output Characteristics

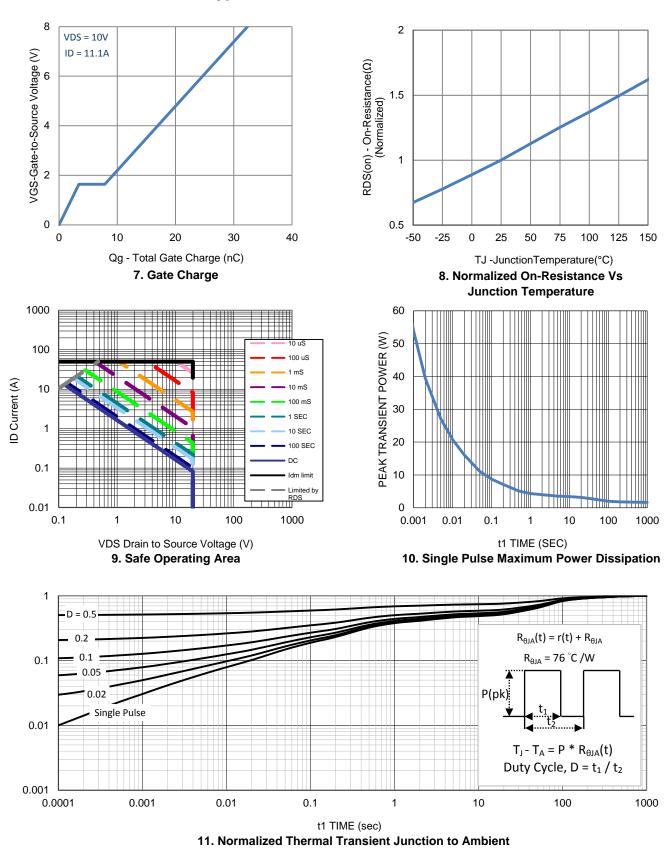






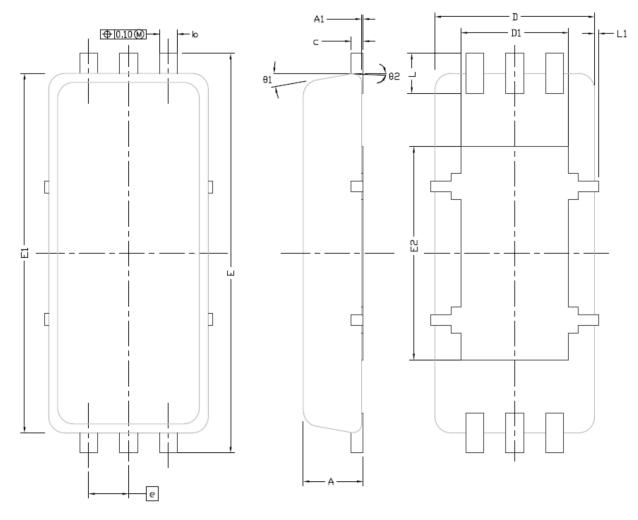
4. Drain-to-Source Forward Voltage





## **Typical Electrical Characteristics**

# Package Information



DIM.	MILLIMETERS			INCHES			
11.12	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.70	0.75	0.80	0.028	0.030	0.0315	
A1	0.00		0.05	0.000		0.002	
b	0.20	0,225	0,30	0.008	0,009	0.012	
С	0.10	0.152	0.20	0.004	0.006	0.008	
D	2.00 BSC			0.079 BSC			
D1	1.30	1.35	1,55	0.051	0.053	0.061	
Ε	5.00 BSC			0197 BSC			
E1	4	1.50 BS	С	0.	0.177 BSC		
E2	2,60	2,67	2,95	0,102	0.105	0.116	
е	0.50 BSC			0.020 BSC			
L	0.40	0.50	0.600	0.016	0.0197	0.0236	
L1	0		0,100	0		0,004	
θ1	0°	10°	12°	0°	10°	12°	
65	3° BSC			3° BSC			